

Description

The H2SK3018T106 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

V_{DS} = 30V I_D =0.1A

 $R_{DS(ON)} < 2.2\Omega @ V_{GS}=10V$

ESD Rating: HBM≥2000V

Application

Battery protection

Load switch

Uninterruptible power supply

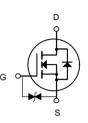
Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
H2SK3018T106	SOT-323	KN	3000

Absolute Maximum Ratings (Tc=25°Cunless otherwise noted)

Symbol	Parameter	Limit	Unit	
Vds	Drain-Source Voltage		30	V
Vgs	Gate-Source Voltage		±20	V
	Continuous Drain Current (T _J =150 $^{\circ}$ C)	T _A =25℃	0.1	
Ι _D		T _A =100 ℃	0.07	A
Ідм	Drain Current-Pulsed (Note 1)		0.65	А
PD	Maximum Power Dissipation	0.35	W	
Тј,Тѕтс	Operating Junction and Storage Temperature Range		-55 To 150	°C
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)		200	°C /W





N-Channel MOSFET



Electrical Characteristics (TA=25°Cunless otherwise noted)

Parameter	Symbol	Test Condition	Min	Тур	Мах	Units
Off Characteristics						
Drain-Source Breakdown Voltage	Vds	Vgs = 0V, Id = 10µA	30			V
Zero Gate Voltage Drain Current	IDSS	V _{DS} =30V,V _{GS} = 0V			0.2	μA
Gate –Source leakage current	lgss	Vgs =±20V, Vds = 0V			±2	μA
Gate Threshold Voltage	VGS(th)	V _{DS} = 3V, I _D =100µA	0.8		1.5	V
Drain-Source On-Resistance	RDS(on)	Vgs = 10V, Id =10mA		1.5	2.2	Ω
Dialit-Source Off-Resistance		Vgs =4.5V,Id =1mA		2	3	Ω
Forward Transconductance	g fs	V _{DS} =3V, I _D = 10mA	20			mS
Dynamic Characteristics*						
Input Capacitance	Ciss			13		pF
Output Capacitance	Coss	VDS =5V,VGS =0V,f =1MHz		9		pF
Reverse Transfer Capacitance	Crss			4		pF
Switching Characteristics*						
Turn-On Delay Time	td(on)			15		ns
Rise Time	tr	Vgs =5V, Vdd =5V,		35		ns
Turn-Off Delay Time	td(off)	I⊳ =10mA, Rg=10Ω, R∟=500Ω,		80		ns
Fall Time	tſ]		80		ns

* These parameters have no way to verify.



H2SK3018T106 N-Channel Enhancement Mode MOSFET

V_{DS}=3V

T**_=25℃**

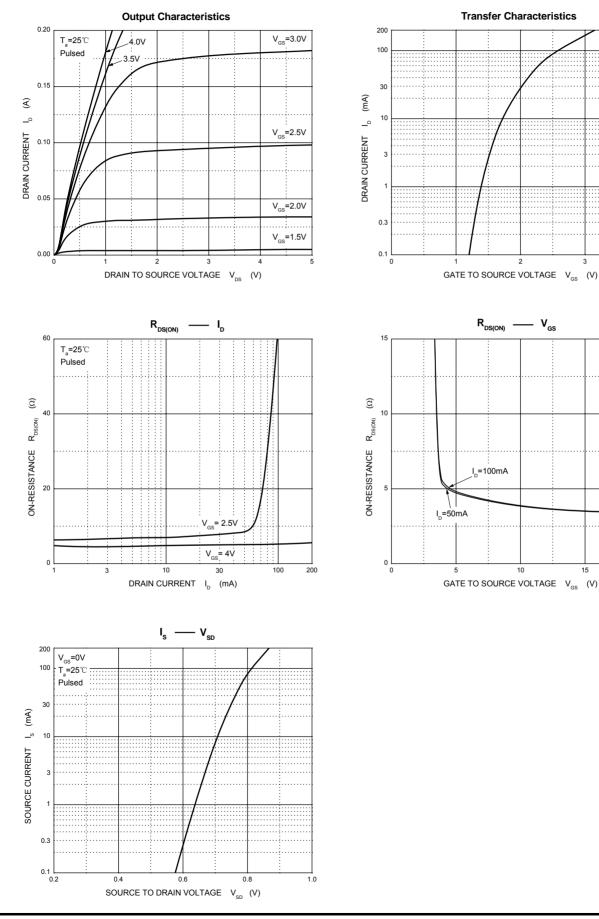
Pulsed

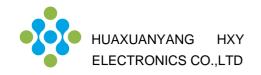
T_=25℃

Pulsed

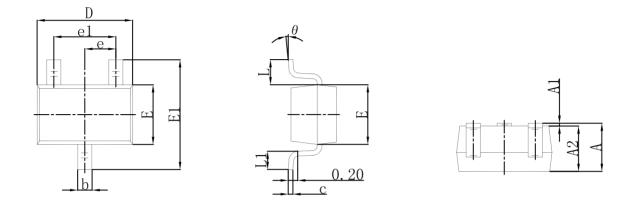
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Typical Characteristics





SOT-323 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
A	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.200	0.400	0.008	0.016	
С	0.080	0.150	0.003	0.006	
D	2.000	2.200	0.079	0.087	
E	1.150	1.350	0.045	0.053	
E1	2.150	2.450	0.085	0.096	
е	0.650	0.650 TYP		6 TYP	
e1	1.200	1.400	0.047	0.055	
L	0.525 REF		0.021 REF		
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	



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